

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR
MANUFACTURING NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is based upon and claims the benefit of priority from Japanese Patent Application No. 2010-258309, filed on Nov. 18, 2010; the entire contents of which are incorporated herein by reference.

FIELD

Embodiments described herein relate generally to a nonvolatile semiconductor memory device and a method for manufacturing a nonvolatile semiconductor memory device.

BACKGROUND

In a nonvolatile semiconductor memory device such as NAND-type flash memory, the distance between adjacent bit lines becomes short if a memory cell is made finer to achieve larger packing densities. Therefore, parasitic capacitance between adjacent gate electrodes increases, which causes a substantial decrease in write speed in a generation of the gate length of a memory cell transistor equal to or smaller than the 10 nm range.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a perspective view illustrating a schematic configuration of a memory cell of a nonvolatile semiconductor memory device according to a first embodiment;

Fig. 2 is a circuit diagram illustrating a schematic configuration of a memory cell array of a nonvolatile semiconductor memory device according to a second embodiment;

Fig. 3 is a plan view illustrating a schematic configuration of an RA part of Fig. 2;

Figs. 4A to 14A, Figs. 4B to 14B, Figs. 15C to 26C,

and Figs. 15D to 26D are cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor memory device according to a third embodiment; and

Figs. 27A to 27D are cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor memory device according to a fourth embodiment.

DETAILED DESCRIPTION

In general, according to one embodiment, a nonvolatile semiconductor memory device includes a memory cell and a gap. The memory cell is provided with a control gate electrode on a charge storage layer via an interelectrode insulating film. The gap is provided between the adjacent charge storage layers in a word line direction, and is formed continuously over the adjacent memory cells in a bit line direction in a manner of sinking below the word line.

Exemplary embodiments of a nonvolatile semiconductor memory device will be explained below in detail with reference to the accompanying drawings. The present invention is not limited to the following embodiments. Additionally, in the explanation, directions such as top, bottom, left and right indicate relative directions in a case where a plane of a side where a memory cell of a semiconductor substrate to be described later is formed is set to be the top. In other words, the directions in the explanation are different from directions in relation to a direction of the acceleration of gravity in some cases. (First Embodiment)

Fig. 1 is a perspective view illustrating a schematic configuration of a memory cell of a nonvolatile semiconductor memory device according to a first embodiment.

In Fig. 1, a trench 2 is formed in a bit line direction DB in a semiconductor substrate 1, and an active area of a memory cell formed on the semiconductor substrate 1 is isolated. Incidentally, the active area in a memory

cell indicates a channel region of a memory transistor provided for a memory cell and a region between memory cells connected in series (source/drain regions, for example). Moreover, it is possible to select a material of the semiconductor substrate 1 from Si, Ge, SiGe, SiC, SiSn, PbS, GaAs, InP, GaP, GaN, GaInAsP, ZnSe, and the like.

Furthermore, a buried insulating film 3 is buried in the trench 2. Incidentally, inorganic polymers that are soluble in organic solvents, such as a CVD oxide film and an ALD oxide film or a CVD oxide film and a SOG oxide film, can be used for the buried insulating film 3. Incidentally, the configuration of the buried insulating film buried in the trench 2 is not necessarily a one-layer structure, and may be two-layered or more.

Moreover, a floating gate electrode 6 is formed for each memory cell via a tunnel insulating film 5 in the active area on the semiconductor substrate 1. The floating gate electrode 6 can be used as a charge storage layer. Incidentally, the tunnel insulating film 5 may be any one of a thermal oxide film and a thermal oxynitride film, for example. Otherwise, it may be any one of a CVD oxide film and a CVD oxynitride film. Otherwise, it may be any one of an insulating film in which Si is interposed and an insulating film in which Si is buried like dots. The floating gate electrode 6 may be any one of polycrystalline silicon to which n- or p-type impurities are doped and a metal or polymetal film using Mo, Ti, W, Al, Ta or the like.

On the floating gate electrode 6, a control gate electrode 8 is formed in a word line direction DW via an interelectrode insulating film 7. Incidentally, the control gate electrode 8 can configure a part of the word line. Here, it is possible to form the control gate electrode 8 around the side walls of the floating gate electrode 6 to improve the coupling ratio between the floating gate electrode 6 and the control gate electrode 8.

A silicide layer 9 is formed on the control gate

electrode 8, and a cover insulating film 10 is formed on the silicide layer 9. Incidentally, any one of a silicon oxide film and a silicon nitride film, for example, can be used as the interelectrode insulating film 7. Otherwise, it may be a layered structure of a silicon oxide film and a silicon nitride film, such as an ONO film. Otherwise, it may be a high dielectric constant film such as aluminum oxide or hafnium oxide, and may be a layered structure of a low dielectric constant film and a high dielectric constant film such as a silicon oxide film and a silicon nitride film. The control gate electrode 8 may be polycrystalline silicon to which any one of n- and p-type impurities are doped. Otherwise, the control gate electrode 8 may be any one of a metal and a polymetal film using Mo, Ti, W, Al, Ta, or the like. If any one of a metal film and a polymetal film is used as the control gate electrode 8, the silicide layer 9 can be omitted. As the silicide layer 9, CoSi, NiSi, PtSi, WSi, MoSi, or the like can be used. Moreover, a silicon oxide film can be used as the cover insulating film 10, for example.

Here, a part of the buried insulating film 3 buried in the trench 2 is removed; accordingly, an air gap AG1 is formed between the adjacent floating gate electrodes 6 in the word line direction DW. The air gap AG1 may be made to reach to a position deeper than an undersurface of the floating gate electrode 6 by being formed in a manner of entering the trench 2. Furthermore, the air gap AG1 can be formed continuously along the trench 2 in a manner of sinking below the control gate electrode 8. Moreover, the interelectrode insulating film 7 can be formed continuously over the adjacent memory cells in the word line direction in a manner of stretching over the air gap AG1. Additionally, the cover insulating film 10 stretches over between the control gate electrodes 8 in a manner of not burying a space between the floating gate electrodes 6 entirely. As a result, an air gap AG2 is formed between

the adjacent floating gate electrodes 6 in the bit line direction DB, and a space is formed on the air gap AG1 between the word lines. Incidentally, the air gap AG2 can be formed in a manner where the top and bottom are asymmetric, and the top end can have the shape of a spire.

Here, the air gaps AG1 and AG2 (the dielectric constant of air is 1, for example) are provided between the floating gate electrodes 6; accordingly, it is possible to reduce parasitic capacitance between the floating gate electrodes compared with a case where an insulator (the dielectric constant of a silicon oxide film is 3.9, for example) is buried between the floating gate electrodes 6. Therefore, it is possible to reduce interference of an electric field between adjacent cells, the interference being caused by parasitic capacitance between the floating gate electrodes, and shorten the distribution width of threshold voltages of cell transistors.

Additionally, the air gap AG1 can reduce fringe capacitance between the control gate electrode 8 and the semiconductor substrate 1 by being formed continuously along the trench 2 in a manner of sinking below the control gate electrode 8. Hence, it is possible to improve the coupling ratio between the floating gate electrode 6 and the control gate electrode 8, and reduce a write voltage. (Second Embodiment)

Fig. 2 is a circuit diagram illustrating a schematic configuration of a memory cell array of a nonvolatile semiconductor memory device according to a second embodiment.

In Fig. 2, cell transistors MT are arranged on a matrix in a row direction and a column direction in a memory cell part R1. Additionally, a plurality of cell transistors MT is connected in series, and select transistors ST are connected at both ends of the series circuits; accordingly, NAND strings NS are configured. Moreover, bit lines BL are arranged in the column direction,

and word lines WL and select gate electrodes SG are arranged in the row direction.

Additionally, the NAND strings NS on the same column are connected to the same bit line BL via the select transistors ST. Additionally, the cell transistors MT on the same row are connected to the same word line WL, and the select transistors ST on the same row are connected to the same select gate electrode SG; accordingly, a NAND block NB is configured.

Furthermore, a word line drawing part R2 is provided next to the memory cell part R1. The word lines WL drawn out from the memory cell part R1 and the select gate electrodes SG are arranged in the word line drawing part R2.

Fig. 3 is a plan view illustrating a schematic configuration of an RA part of Fig. 2.

In Fig. 3, the trenches TC are formed in a bit line direction DB, and an active area AA is isolated by the trenches TC. Moreover, the word lines WL and the select gate electrodes SG are formed in a word line direction DW. Additionally, a bit contact part R3 is provided between the select gate electrodes SG, and bit contacts BC are formed on the active area AA of the bit contact part R3. Furthermore, on the active area AA of the word line drawing part R2, word contacts WC contacting the word lines WL drawn out from the memory cell part R1 are provided while select gate contacts SC contacting the select gate electrodes SG drawn out from the memory cell part R1 are provided.

Additionally, in the trench TC of the memory cell part R1, a part of the buried insulating film 3 of Fig. 1 is removed; accordingly, the air gap AG1 is formed along the trench 2 in the memory cell part R1. Furthermore, in the trench TC of the word line drawing part R2, the buried insulating film 3 of Fig. 1 is made not to be removed; accordingly, the air gap AG1 is not formed in the word line drawing part R2. Here, the air gap AG1 is formed

continuously over the adjacent memory cells in a manner of sinking below the control gate electrode 8 while being separated below the select gate electrode SG. Moreover, in the trench TC of the bit contact part R3, a reburied insulating film RB is reburied in the air gap AG1; accordingly, the air gap AG1 is disappeared in the bit contact part R3.

Here, it is possible to prevent the fine word line WL from staying floating in the air above the wide trench TC of the word line drawing part R2 by causing the air gap AG1 not to form in the word line drawing part R2. As a result, it is possible to prevent pattern hops, pattern collapse and the like, and it is possible to control the occurrence of short failures, and the like between the word lines WL.

Additionally, in the trench TC of the bit contact part R3, the air gap AG1 is reburied with the reburied insulating film RB. As a result, also in a case where the position of the bit contact BC deviates to any one of the right and the left trench TC side, it is possible to prevent the bit contact BC from penetrating the substrate via the air gap AG1.

(Third Embodiment)

Figs. 4A to 14A, Figs. 4B to 14B, Figs. 15C to 26C, and Figs. 15D to 26D are cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor memory device according to a third embodiment. Incidentally, Figs. 4B to 12B, Fig. 15C, Fig. 17C, and Figs. 19B to 26B are cross-sectional views cut along the A-A line of Fig. 3, Figs. 4A to 12A, Fig. 16C, and Fig. 18C are cross-sectional view cut along the A'-A' line of Fig. 3, Figs. 13A to 15A, Fig. 17A, Figs. 19C to 26C are cross-sectional views cut along the B-B line of Fig. 3, Fig. 13B, Fig. 16A, and Fig. 18A are cross-sectional views cut along the B'-B' line of Fig. 3, Fig. 14B, Fig. 15B, Fig. 17B, Figs. 19D to 26D are cross-sectional views cut along the C-C line of Fig. 3, Figs. 16B and 18B are cross-sectional

views cut along the C'-C' line of Fig. 3, Fig. 15D, Fig. 17D, Figs. 19A to 26A are cross-sectional views cut along the D-D line of Fig. 3, and Figs. 16D and 18D are cross-sectional views cut along the D'-D' line of Fig. 3.

In Figs. 4A and 4B, the tunnel insulating film 5 is formed on the semiconductor substrate 1 by use of a method such as thermal oxidation. Moreover, a floating gate electrode material 6' is deposited on the tunnel insulating film 5 by use of a method such as CVD.

Next, as shown in Figs. 5A and 5B, a hard mask M1 is formed on the floating gate electrode material 6' by use of a method such as CVD. Incidentally, it is possible to use any one of a silicon oxide film and a silicon nitride film as the hard mask M1, for example.

Next, as shown in Figs. 6A and 6B, a resist pattern R1 provided with openings K1 and K1' is formed on the hard mask M1 by use of photolithography techniques.

Next, as shown in Figs. 7A and 7B, after the hard mask M1 is patterned by using the resist pattern R1 as a mask, trenches 2 and 2' are formed in the semiconductor substrate 1 by etching the floating gate electrode material 6', the tunnel insulating film 5 and the semiconductor substrate 1 by using the hard mask M1 as a mask.

Next, as shown in Figs. 8A and 8B, the buried insulating film 3 is formed on the hard mask M1 such that the entire trenches 2 and 2' are buried by use of a method such as CVD or SOG (coating).

Next, as shown in Figs. 9A and 9B, the buried insulating film 3 is made thinner, and a surface of the hard mask M1 is exposed by use of a method such as CMP.

Next, as shown in Figs. 10A and 10B, the hard mask M1 is removed by use of a method such as wet etching. Incidentally, in a case where the hard mask M1 is a silicon nitride film, it is possible to use hot phosphoric acid as a chemical solution for wet etching. A part of the buried insulating film 3 is then removed by use of anisotropic

etching such as RIE, and a part of the side walls of the floating gate electrode material 6' is exposed. Incidentally, in a case of exposing a part of the side walls of the floating gate electrode material 6', it is preferable that the buried insulating film 3 should remain above the tunnel insulating film 5. Moreover, in a case where the buried insulating film 3 is a SOG oxide film, a part of the buried insulating film 3 may be removed by wet etching while using dilute hydrofluoric acid.

Next, as shown in Figs. 11A and 11B, the interelectrode insulating film 7 is formed on the floating gate electrode material 6' such that the side walls of the floating gate electrode material 6' are covered by use of a method such as CVD. Incidentally, the interelectrode insulating film 7 may be a multi-layered structure such as an ONO film.

Next, as shown in Figs. 12A and 12B, a control gate electrode material 8' is deposited on the interelectrode insulating film 7 by use of a method such as CVD.

Next, as shown in Figs. 13A and 13B, a cap insulating film 11 is formed on the control gate electrode material 8' by use of a method such as CVD. Incidentally, it is possible to use any one of a silicon oxide film and a silicon nitride film, for example, as the cap insulating film 11. Additionally, the cap insulating film 11 is coated with a resist film R2 by use of a method such as spin coating.

Next, as shown in Figs. 14A and 14B, an opening K2 is formed in the resist film R2 by use of photolithography techniques.

Next, as shown in Figs. 15A to 15D and Figs. 16A to 16D, after the cap insulating film 11 is patterned by using the resist film R2 provided with the opening K2 as a mask, the control gate electrode material 8', the interelectrode insulating film 7, and the floating gate electrode material 6' are etched by using the cap insulating film 11 as a

mask; accordingly, the floating gate electrode 6 separated on a memory cell basis is formed while the control gate electrode 8 and a select gate electrode 12, which are arranged on the floating gate electrodes 6 via the interelectrode insulating films 7, are formed in the word line direction. Here, the select gate electrode 12 is connected, via an opening K2' provided for the interelectrode insulating film 7, to the underlying floating gate electrode 6.

Here, assuming that the buried insulating film 3 and the interelectrode insulating film 7 are made up of a film of similar material such as a silicon oxide film, the buried insulating film 3 is etched by the amount that the interelectrode insulating film 7 of the side walls of the floating gate electrode 6 is etched in a longitudinal direction. As a result, the drop amount X of the buried insulating film 3 of when viewed from an undersurface of the interelectrode insulating film 7 on the trenches 2 and 2' at this time almost agrees with a height X on the trenches 2 and 2' from the undersurface of the interelectrode insulating film 7 to a top surface of the interelectrode insulating film 7 on the charge storage layer 6. Furthermore, the selectivity between the buried insulating film 3 and the floating gate electrode material 6' is not 100%. Therefore, the buried insulating film 3 is etched also when the floating gate electrode material 6' is etched, and the buried insulating film 3 further drops by an amount of α ($\alpha < X$).

Next, as shown in Figs. 17A to 17D and Figs. 18A to 18D, a resist pattern R3 is formed on the buried insulating film 3 and the cap insulating film 11 such that the word line drawing part R2 of Fig. 3 is covered by use of photolithography techniques. A part of the buried insulating film 3 of the memory cell part R1 of Fig. 3 is then removed along the trench 2 by use of a method such as wet etching, and the air gap AG1 is formed between the

adjacent floating gate electrodes 6 in the word line direction DW. At this time, it is possible to form the air gap AG1 continuously along the trench 2 in a manner of sinking below the control gate electrode 8. Moreover, the air gap AG1 is split below the select gate electrode 12; accordingly, the buried insulating film 3 can remain completely in a height direction below a part of the select gate electrode 12.

Here, it is necessary to etch the buried insulating film 3 in a lateral direction by a gate length L of the control gate electrode in order to link the air gap AG1 below the control gate electrode 8 on the trench 2. At this time, in a case of etching the buried insulating film 3 in a lateral direction, the buried insulating film 3 is etched from both sides. Therefore, the buried insulating film 3 further drops by $L/2$ from the states of Figs. 15A to 15D. Assuming that the over-etch amount of the buried insulating film 3 at this time is β ($\beta < L/2$), a depth D of the air gap AG1 of when viewed from the top surface of the interelectrode insulating film 7 on the trench 2 is $X + \alpha + L/2 + \beta$.

In other words, considering the condition of $\alpha < X$ and $\beta < L/2$, the depth D of the air gap AG1 of when viewed from the top surface of the interelectrode insulating film 7 on the trench 2 satisfies a condition of $X + L/2 \leq D < 2X + L$.

Here, the depth D of the air gap AG1 is set in a manner of satisfying the condition of $X + L/2 \leq D < 2X + L$; accordingly, it is possible to suppress the etching amount of the buried insulating film 3 to a minimum and form the air gap AG1 such that the air gap AG1 links below the control gate electrode 8. Consequently, it is possible to control the etching of the tunnel insulating film 5 and the interelectrode insulating film 7 upon etching the buried insulating film 3 while reducing interference of an electric field between the adjacent cells, the interference

being caused by parasitic capacitance between the floating gate electrodes 6.

Moreover, the word line drawing part R2 is covered with the resist pattern R3 upon the wet etching of the buried insulating film 3; accordingly, it is possible not to form the air gap AG1 in the word line drawing part R2. Therefore, it is possible to prevent the fine word line WL from staying floating in the air above the wide trench TC in the word line drawing part R2 and prevent pattern hops, pattern collapse and the like.

Next, as shown in Figs. 19A to 19D, a spacer insulating film 13 is formed in a manner of covering an entire exposed surface by use of a method such as CVD. Incidentally, it is possible to use a silicon oxide film, for example, as the spacer insulating film 13.

Next, as shown in Figs. 20A to 20D, the cover insulating film 10 is formed in a manner of stretching over between the control gate electrodes 8 to form the air gap AG2 between the adjacent floating gate electrodes 6 in the bit line direction DB by use of a method such as plasma CVD. Incidentally, it is possible to use a silicon oxide film, for example, as the cover insulating film 10. Moreover, in a case of forming the cover insulating film 10 on the control gate electrode 8, it is possible to set a condition at poor coverage to prevent the air gaps AG1 and AG2 from being buried by the cover insulating film 10.

Next, as shown in Figs. 21A to 21D, the cover insulating film 10 of the bit contact part R3 of Fig. 3 is removed by use of photolithography techniques and dry etching techniques.

Next, as shown in Figs. 22A to 22D, a reburied insulating film 14 is formed on the cover insulating film 10 such that the inside of the trench 2 of the bit contact part R3 is reburied by use of a method such as CVD. Incidentally, it is possible to use a silicon oxide film, for example, as the reburied insulating film 14.

Next, as shown in Figs. 23A to 23D, a stopper film 15 is formed on the reburied insulating film 14 by use of a method such as CVD. Incidentally, it is possible to use a silicon nitride film, for example, as the stopper film 15.

Next, as shown in Figs. 24A to 24D, an interlayer insulating film 16 is formed on the stopper film 15 by use of a method such as CVD. Incidentally, it is possible to use, for example, any one of a NSG film, a PSG film, a BSG film, a BPSG film and a HDP film, for example, as the interlayer insulating film 16. The interlayer insulating film 16 is planarized by performing CMP by using the stopper film 15 as a stopper.

Next, as shown in Figs. 25A to 25D, an opening 17 corresponding to the bit contact BC of Fig. 3 is formed in the interlayer insulating film 16 by use of photolithography techniques and dry etching techniques.

Next, as shown in Figs. 26A to 26D, a contact electrode 18 is buried in the opening 17 to form the bit contact BC of the bit contact part R3 of Fig. 3. Incidentally, it is possible to use metal such as n^+ polycrystalline silicon and W for the contact electrode 18.

Here, it is possible to prevent the opening 17 from penetrating the semiconductor substrate 1 by reburying the inside of the trench 2 of the bit contact part R3 with the reburied insulating film 14, even if the position of the opening 17 deviates to the trench 2 side.

(Fourth Embodiment)

Figs. 27A to 27D are cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor memory device according to a fourth embodiment. Incidentally, Fig. 27A is a cross-sectional view cut along the D-D line of Fig. 3, Fig. 27B is a cross-sectional view cut along the A-A line of Fig. 3, Fig. 27C is a cross-sectional view cut along the B-B line of Fig. 3, and Fig. 27D is a cross-sectional view cut along the C-C line of Fig. 3.

The description was given of the method for forming the cover insulating film 10 in the step of Figs. 20A to 20D after forming the spacer insulating film 13 in the step of Figs. 19A to 19D in the above-mentioned third embodiment; however, the cover insulating film 10 may be formed in the step of Figs. 20A to 20D without forming the spacer insulating film 13 in the step of Figs. 19A to 19D in Figs. 27A to 27D.

Here, the omission of the spacer insulating film 13 enables the air gaps AG1 and AG2 to expand by the thickness of the spacer insulating film 13 and parasitic capacitance between the floating gate electrodes 6 to further reduce.

Incidentally, in a case of omitting the spacer insulating film 13, it is possible to rebury the inside of the trench 2 of the bit contact part R3 by adjusting the thickness of any one of the reburied insulating film 14 and the stopper film 15.

While certain embodiments have been described, these embodiments have been presented by way of example only, and are not intended to limit the scope of the inventions. Indeed, the novel embodiments described herein may be embodied in a variety of other forms; furthermore, various omissions, substitutions and changes in the form of the embodiments described herein may be made without departing from the spirit of the inventions. The accompanying claims and their equivalents are intended to cover such forms or modifications as would fall within the scope and spirit of the inventions.

What is claimed is:

1. A nonvolatile semiconductor memory device comprising:
a memory cell provided with a control gate electrode on a charge storage layer via an interelectrode insulating film; and
a gap provided between the adjacent charge storage layers in a word line direction and formed continuously over the adjacent memory cells in a bit line direction in a manner of sinking below the word line.
2. The nonvolatile semiconductor memory device according to claim 1, wherein the gap is formed along a trench isolating an active area of the memory cell.
3. The nonvolatile semiconductor memory device according to claim 2, wherein the gap enters the trench that isolates the active area of the memory cell and is provided in a semiconductor substrate.
4. The nonvolatile semiconductor memory device according to claim 3, wherein the gap is formed continuously in the trench over the adjacent memory cells in the bit line direction.
5. The nonvolatile semiconductor memory device according to claim 1, further comprising a space formed on the gap between the word lines.
6. The nonvolatile semiconductor memory device according to claim 1, further comprising a cover insulating film stretching over between the control gate electrodes in a manner.
7. The nonvolatile semiconductor memory device according to claim 1, wherein the gap is arranged in a manner where the interelectrode insulating film covers side walls of the

charge storage layer.

8. The nonvolatile semiconductor memory device according to claim 2, wherein assuming a gate length of the control gate electrode is L, and a height on the trench from an undersurface of the interelectrode insulating film to a top surface of the interelectrode insulating film on the charge storage layer is X, a depth D of the gap of when viewed from the top surface of the interelectrode insulating film on the trench satisfies a condition of $X + L/2 \leq D < 2X + L$.

9. The nonvolatile semiconductor memory device according to claim 1, wherein the gap reaches to a position deeper than an undersurface of the charge storage layer.

10. The nonvolatile semiconductor memory device according to claim 1, further comprising a select gate electrode connecting an active area of the memory cell to the bit line, wherein the gap is separated below the select gate electrode.

11. The nonvolatile semiconductor memory device according to claim 1, further comprising:

- a word line drawing part in which the word line drawn out from the memory cell is arranged;

- and a buried insulating film buried the trench, wherein the buried insulating film is in contact with the interelectrode insulating film on the trench isolating the active area of the word line drawing part.

12. The nonvolatile semiconductor memory device according to claim 1, further comprising:

- a bit contact part in which a bit contact is formed;
- and

- a reburied insulating film reburying the gap formed in a trench isolating an active area of the bit contact part.

13. The nonvolatile semiconductor memory device according to claim 2, wherein the interelectrode insulating film is formed continuously over the adjacent memory cells in the word line direction in a manner of stretching over the gap.

14. The nonvolatile semiconductor memory device according to claim 13, wherein the interelectrode insulating film is arranged in a position lower than a top of the charge storage layer on the gap.

15. A method for manufacturing a nonvolatile semiconductor memory device, comprising:

- depositing a floating gate electrode material on a semiconductor substrate via a tunnel insulating film;

- forming a trench in the semiconductor substrate in a bit line direction via the floating gate electrode material and the tunnel insulating film;

- forming a buried insulating film in the trench;

- forming an interelectrode insulating film on the buried insulating film and the floating gate electrode material;

- depositing a control gate electrode material on the interelectrode insulating film;

- forming a floating gate electrode separated on a memory cell basis by patterning the control gate electrode material, the interelectrode insulating film, and the floating gate electrode material while forming a control gate electrode arranged on the floating gate electrode in a word line direction; and

- forming a gap arranged along the trench in a manner of sinking below the word line between the adjacent floating gate electrode in the word line direction by removing at least a part of the buried insulating film buried in the trench.

16. The method for manufacturing a nonvolatile semiconductor memory device according to claim 15, further comprising forming a cover insulating film stretching over between the control gate electrodes in a manner where the gap is not buried.

17. The method for manufacturing a nonvolatile semiconductor memory device according to claim 16, further comprising a space formed on the gap between the word lines.

18. The method for manufacturing a nonvolatile semiconductor memory device according to claim 15, wherein the interelectrode insulating film is formed continuously over the adjacent memory cells in the word line direction in a manner of stretching over the gap.

19. The method for manufacturing a nonvolatile semiconductor memory device according to claim 15, further comprising covering a word line drawing part in which the word line drawn out from the memory cell is arranged with a resist upon removing at least a part of the buried insulating film buried in the trench.

20. The method for manufacturing a nonvolatile semiconductor memory device according to claim 15, further comprising reburying the gap formed in the trench isolating an active area of a bit contact part in which a bit contact is formed with a reburied insulating film after removing at least a part of the buried insulating film buried in the trench.